VSP-MIKRON	V_{RRM}=1700V I_F =100A **Diode-Die** **KD100170F** Die Size-10.8 x 8.3мм.

Ultra low losses

Preliminary

Passivation : Silicon Oxide plus Polyimide

Maximum rated values

Parameter	Symbol	Unit	min	max
Repetitive peak reverse voltage	V_{RRM}	V	-	1700
Continuous forward current	I_F	A	-	100
Repetitive peak forward current *	I_{FRM}	A	-	200
Junction temperature	T_{vj}	˚C	-	150

***Limited by** $T_{vj\ max}$

Diode Characteristics values

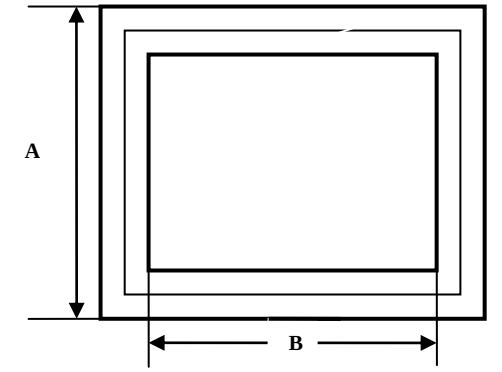
Parameter	Symbol	Conditions	min	typ	max	Unit
Continuous forward voltage	V_F	I_F=100A,T_{vj}= 25˚C		2.4		V
Continuous reverse current	I_R	V_R=1800V T_{vj}= 25˚C			100	uA
		T_{vj}= 125˚C		2.5		mA
Peak reverse recovery current	I_{RRM}	I_F=100A, V_R=700V, dI_F/dt=200A/uS, T_{vj}= 25˚C		tbd		A
Recovered charge	Q_{rr}			tbd		µC
Reverse Recovery Time	t_{rr}			tbd		nS
Reverse Recovery Time	t_{rr}	I_F=1A, V_R=30V, dI_F/dt=200A/uS.		100	120	nS

Mechanical properties

Top metal: ***Al-Ti*** – for Wire Bonding.

Backside metal: ***Ti-Ni-Ag –*** for Soldering.

DIM	ITEM	µm
A_X A_y	Die Size	10800 8300
D	Thickness	460max.
Scribe line Width		60



Top Metal